Access DB# 162205

SEARCH REQUEST FORM

Scientific and Technical Information Center

Requester's Full Name: Sin J. Lee Examiner #: 76060 Date: 8-10-2005
Art Unit: 1752 Phone Number 30 2-1333 Serial Number: 10/669,492
Mail Box and Bldg/Room Location: Rem. 9D60 Results Format Preferred (circle): PAPER DISK E-MAIL

If more than one search is submitted, please prioritize searches in order of need.

****

Please provide a detailed statement of the search topic, and describe as specifically as possible the subject matter to be searched. Include the elected species or structures, keywords, synonyms, acronyms, and registry numbers, and combine with the concept or utility of the invention. Define any terms that may have a special meaning. Give examples or relevant citations, authors, etc, if known. Please attach a copy of the cover sheet, pertinent claims, and abstract.

Title of Invention: PR. see B-6.

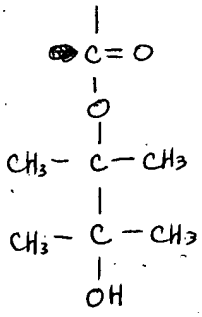
Inventors (please provide full names):

Earliest Priority Filing Date:

SCIENTIFIC REFERENCE BR
Sci & Tech Inf Ctr
AUG 1 RECD
Pat. & T.M. Office

**For Sequence Searches Only* Please include all pertinent information (parent, child, divisional, or issued patent numbers) along with the appropriate serial number.*

Please search for a polymer having the following functional gp. in its structure



This polymer is used in a photosensitive, or photoresist or resist composition

(Please don't limit the search ~~[illegible]~~ - If you have to, Please call me. Thanks!)

****

STAFF USE ONLY	Type of Search	Vendors and cost where applicable
Searcher: EJ	NA Sequence (#)	STN
Searcher Phone #:	AA Sequence (#)	Dialog
Searcher Location:	Structure (#)	Questel/Orbit
Date Searcher Picked Up:	Bibliographic	Dr.Link
Date Completed: 8-23-05	Litigation	Lexis/Nexis
Searcher Prep & Review Time:	Fulltext	Sequence Systems
Clerical Prep Time:	Patent Family	WWW/Internet
Online Time:	Other	Other (specify)

PTO-1590 (8-01)

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FILE 'REGISTRY' ENTERED AT 17:16:21 ON 23 AUG 2005
USE IS SUBJECT TO THE TERMS OF YOUR STN CUSTOMER AGREEMENT.
PLEASE SEE "HELP USAGETERMS" FOR DETAILS.
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=> d his


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               SAV L4 LEE492/A

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L5            0 S L4

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L6            4 S L4

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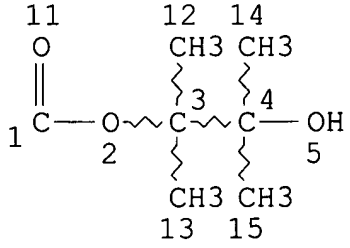


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NODE ATTRIBUTES:
DEFAULT MLEVEL IS ATOM
DEFAULT ECLEVEL IS LIMITED

GRAPH ATTRIBUTES:
RING(S) ARE ISOLATED OR EMBEDDED
NUMBER OF NODES IS  10
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STEREO ATTRIBUTES: NONE
L2 SCR 2043
L4 10 SEA FILE=REGISTRY SSS FUL L1 AND L2

100.0% PROCESSED 512 ITERATIONS 10 ANSWERS
SEARCH TIME: 00.00.01

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USE IS SUBJECT TO THE TERMS OF YOUR STN CUSTOMER AGREEMENT.
PLEASE SEE "HELP USAGETERMS" FOR DETAILS.

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L6 ANSWER 1 OF 4 ZCAPLUS COPYRIGHT 2005 ACS on STN
AN 2005:300739 ZCAPLUS
DN 142:382169
ED Entered STN: 07 Apr 2005
TI Low-polydispersity photoimaging polymers and photoresists and processes for microlithography
IN Feiring, Andrew Edward; Fryd, Michael; Schadt, Frank L., III
PA E.I. Dupont De Nemours and Co., USA
SO PCT Int. Appl., 41 pp.
CODEN: PIXXD2
DT Patent
LA English
IC ICM G03F007-004
ICS C08F220-10; C08F220-22; C08F232-00; C08F002-32
CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)
Section cross-reference(s): 35, 38
FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	WO 2005031462	A1	20050407	WO 2004-US31247	200409 22
	WO 2005031462	B1	20050602		

W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW,

MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD,
SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ,
VC, VN, YU, ZA, ZM, ZW
RW: BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW,
AM, AZ, BY, KG, KZ, MD, RU, TJ, TM, AT, BE, BG, CH, CY, CZ,
DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PL,
PT, RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ,
GW, ML, MR, NE, SN, TD, TG

US 2005112495 A1 20050526 US 2004-945124 200409 20

PRAI US 2003-505077P P 20030923

CLASS

PATENT NO.	CLASS	PATENT FAMILY CLASSIFICATION CODES
WO 2005031462	ICM	G03F007-004
	ICS	C08F220-10; C08F220-22; C08F232-00; C08F002-32
WO 2005031462	ECLA	C09D133/14
US 2005112495	NCL	430/270.100

AB The invention pertains to low polydispersity copolymers useful for photoimaging and photoresist compns., and to the photoimaging processes which use these compns. The low polydispersity copolymers of this invention are prepd. using controlled radical polymn. (CRP) techniques, such as RAFT (reversible addn. fragmentation chain transfer) polymn.

ST polydispersity photoimaging polymer photoresist microlithog

IT Lithography
Photoresists
Polydispersity
(low-polydispersity photoimaging polymers for photoresists and microlithog.)

IT **849429-45-4P 849429-47-6P 849429-49-8P**
(low-polydispersity photoimaging polymers for photoresists and microlithog.)

RE.CNT 3 THERE ARE 3 CITED REFERENCES AVAILABLE FOR THIS RECORD

RE

(1) Consortium Fuer Elektrochemische Industrie Gmbh; EP 0990666 A 2000 ZCAPLUS
(2) Leslie, G; US 6303724 B1 2001 ZCAPLUS
(3) Shang-Wern, C; US 6441115 B1 2002 ZCAPLUS

IT **849429-45-4P 849429-47-6P 849429-49-8P**
(low-polydispersity photoimaging polymers for photoresists and microlithog.)

RN 849429-45-4 ZCAPLUS

CN 2-Propenoic acid, 3-hydroxytricyclo[3.3.1.13,7]dec-1-yl ester, polymer with 2-[(bicyclo[2.2.1]hept-5-en-2-yloxy)methyl]-1,1,1,3,3,3-hexafluoro-2-propanol, 2-hydroxy-1,1,2-trimethylpropyl 2-propenoate and tetrafluoroethene (9CI) (CA INDEX NAME)

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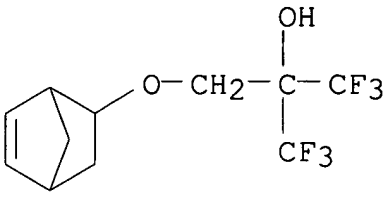

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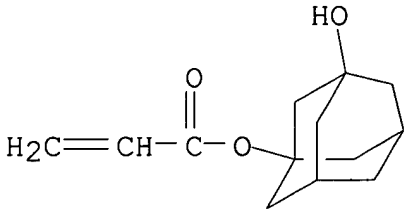

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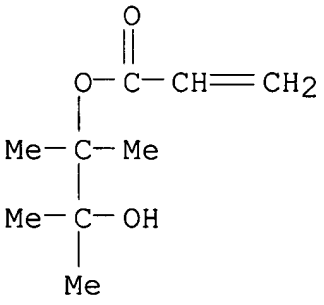
CMF C9 H16 O3



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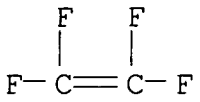

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CN 2-Propenoic acid, 3-hydroxytricyclo[3.3.1.13,7]dec-1-yl ester, polymer with 2-[(bicyclo[2.2.1]hept-5-en-2-yloxy)methyl]-1,1,1,3,3,3-hexafluoro-2-propanol, 2-hydroxy-1,1,2-trimethylpropyl 2-propenoate, 2-methyltricyclo[3.3.1.13,7]dec-2-yl 2-propenoate and tetrafluoroethene (9CI) (CA INDEX NAME)

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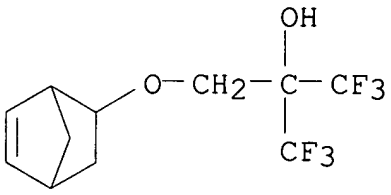

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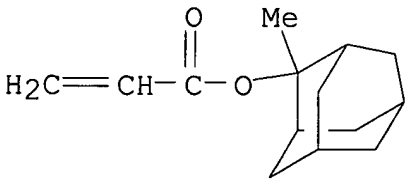

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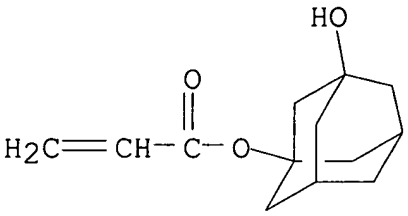

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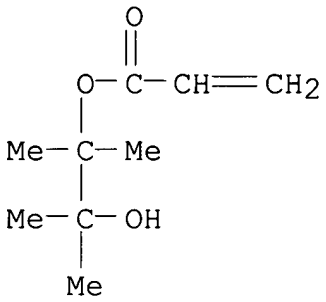

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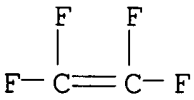

RN 849429-49-8 ZCAPLUS
CN 2-Propenoic acid, 3-hydroxytricyclo[3.3.1.13,7]dec-1-yl ester, polymer with 2-[(bicyclo[2.2.1]hept-5-en-2-yloxy)methyl]-1,1,1,3,3,3-

hexafluoro-2-propanol, 2-hydroxy-1,1,2-trimethylpropyl 2-propenoate and 2-methyltricyclo[3.3.1.13,7]dec-2-yl 2-propenoate (9CI) (CA INDEX NAME)

CM 1

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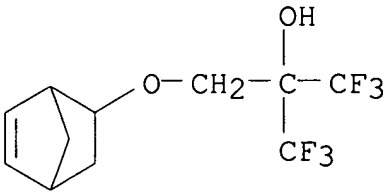

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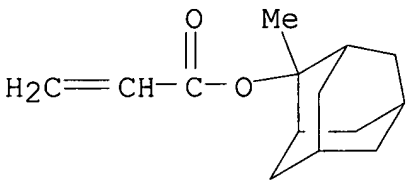

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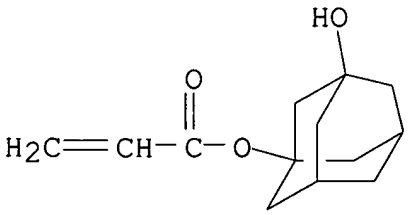

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CRN 97325-36-5
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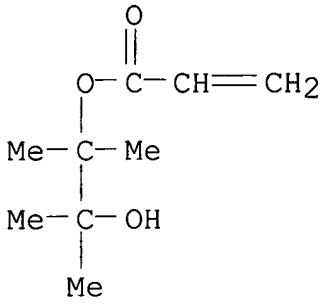

L6 ANSWER 2 OF 4 ZCAPLUS COPYRIGHT 2005 ACS on STN
AN 2005:300738 ZCAPLUS
DN 142:382168
ED Entered STN: 07 Apr 2005
TI Low-polydispersity photoimageable acrylic polymers for photoresists and processes for microlithography
IN Farnham, William Brown; Fryd, Michael; Schadt, Frank Leonard, III
PA E.I. Dupont De Nemours and Co., USA
SO PCT Int. Appl., 37 pp.
CODEN: PIXXD2
DT Patent
LA English
IC ICM G03F007-004
ICS C08F020-10; C08F020-22; C08F002-38; C09D133-14; C07C035-29; C07C069-54
CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)
Section cross-reference(s): 38
FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI WO 2005031461	A1	20050407	WO 2004-US31242	20040922

W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW,

MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD,
SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ,
VC, VN, YU, ZA, ZM, ZW
RW: BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW,
AM, AZ, BY, KG, KZ, MD, RU, TJ, TM, AT, BE, BG, CH, CY, CZ,
DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PL,
PT, RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ,
GW, ML, MR, NE, SN, TD, TG

US 2005119378 A1 20050602 US 2004-943063 200409 16

PRAI US 2003-505038P P 20030922

CLASS

PATENT NO.	CLASS	PATENT FAMILY CLASSIFICATION CODES
WO 2005031461	ICM	G03F007-004
	ICS	C08F020-10; C08F020-22; C08F002-38; C09D133-14; C07C035-29; C07C069-54
WO 2005031461	ECLA	C07C035/29
US 2005119378	NCL	524/104.000
	ECLA	C07C035/29

AB There remains a need for photoresists with high transparency at 157-248 nm and good resoln. to enable the prodn. of electronic components with smaller and smaller feature sizes. The invention pertains to low polydispersity acrylic polymers useful for photoimaging and photoresist compns., and to the photoimaging processes which use these compns. The low polydispersity polymers of this invention are prepd. using controlled radical polymn. (CRP) techniques, such as RAFT (reversible addn. fragmentation chain transfer) polymn.

ST reversible addn fragmentation chain transfer polymn polymer acrylic photoresist; low polydispersity photoimageable acrylic polymer photoresist

IT Photolithography
Photoresists
(low-polydispersity photoimageable acrylic polymers for photoresists and processes for microlithog.)

IT **849595-85-3P 849595-86-4P** 849595-87-5P
849595-88-6P
(low-polydispersity photoimageable acrylic polymers for photoresists)

IT 497-38-1DP, Bicyclo[2.2.1]heptan-2-one, enolate deriv.; reaction products with hexafluorobutene epoxide 497-38-1DP, Norcamphor, reaction products with hexafluorobutene epoxide 84802-91-5DP, reaction products with bicycloheptanone enolate deriv. 84802-91-5DP, reaction products with norcamphor 824410-98-2P 824411-04-3P
(prepn. of low-polydispersity photoimageable acrylic polymers)

IT 760-93-0, Methacrylic anhydride
(prepn. of low-polydispersity photoimageable acrylic polymers)
RE.CNT 5 THERE ARE 5 CITED REFERENCES AVAILABLE FOR THIS RECORD
RE
(1) Central Glass Company Limited; EP 1103856 A 2001 ZCAPLUS
(2) E I Du Pont de Nemours And Company; WO 9931144 A 1999 ZCAPLUS
(3) Feiring; WO 03075094 A1 2003 ZCAPLUS
(4) Shang-Wern, C; US 6441115 B1 2002 ZCAPLUS
(5) Shipley Company Llc; WO 03077029 A1 2003 ZCAPLUS
IT **849595-85-3P 849595-86-4P 849595-88-6P**
(low-polydispersity photoimageable acrylic polymers for photoresists)
RN 849595-85-3 ZCAPLUS
CN 2-Propenoic acid, 2-methyl-, 3-[3,3,3-trifluoro-2-hydroxy-2-(trifluoromethyl)propyl]bicyclo[2.2.1]hept-2-yl ester, polymer with 2-hydroxy-1,1,2-trimethylpropyl 2-propenoate (9CI) (CA INDEX NAME)

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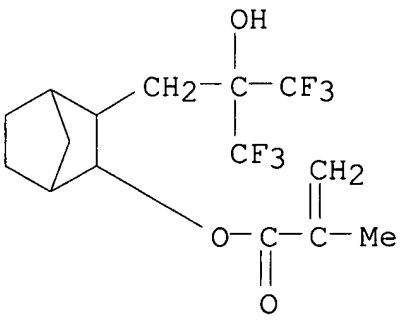

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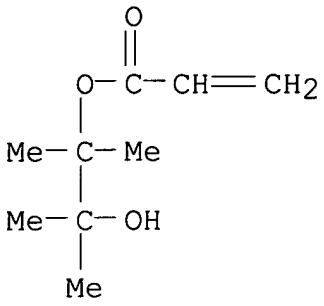

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CN 2-Propenoic acid, 2-methyl-, 2-methyltricyclo[3.3.1.13,7]dec-2-yl ester, polymer with 2-hydroxy-1,1,2-trimethylpropyl 2-propenoate and 3-[3,3,3-trifluoro-2-hydroxy-2-(trifluoromethyl)propyl]bicyclo[2.2.1]hept-2-yl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

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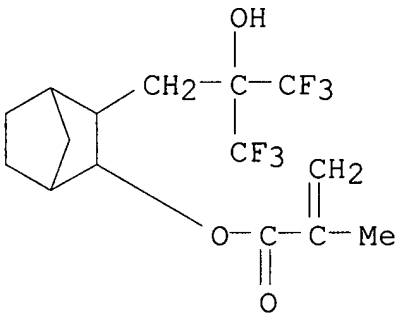

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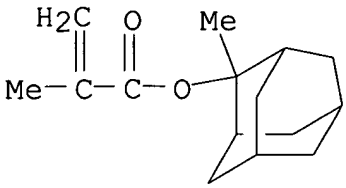

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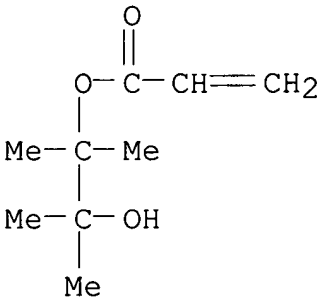

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CN 2-Propenoic acid, 2-methyl-, 3-hydroxytricyclo[3.3.1.13,7]dec-1-yl ester, polymer with 2-hydroxy-1,1,2-trimethylpropyl 2-propenoate, 2-methyltricyclo[3.3.1.13,7]dec-2-yl 2-methyl-2-propenoate and 3-[3,3,3-trifluoro-2-hydroxy-2-(trifluoromethyl)propyl]bicyclo[2.2.1]hept-2-yl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

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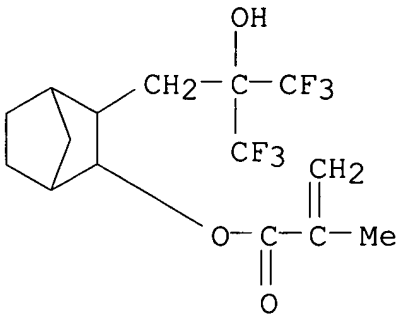

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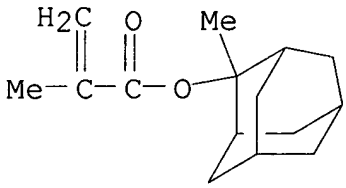

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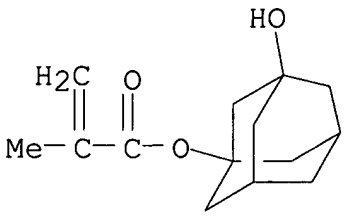

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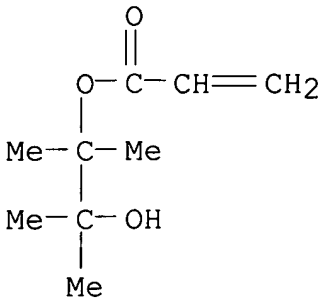


L6 ANSWER 3 OF 4 ZCAPLUS COPYRIGHT 2005 ACS on STN
AN 2005:238519 ZCAPLUS
DN 142:325922
ED Entered STN: 18 Mar 2005
TI Preparation and use of exo-2-fluoroalkyl(bicyclo[2.2.1]hept-5-enes)
IN Feiring, Andrew Edward; Petrov, Viacheslav Alexandrovich; Schadt, Frank Leonard
PA USA
SO U.S. Pat. Appl. Publ., 17 pp.
CODEN: USXXCO
DT Patent
LA English
IC ICM G03C001-492
INCL 430270100
CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)
Section cross-reference(s): 35, 38
FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
US 2005058932	A1	20050317	US 2003-664303	200309 16
US 6875555	B2	20050405		

PRAI US 2003-664303 20030916
CLASS

PATENT NO.	CLASS	PATENT FAMILY CLASSIFICATION CODES
US 2005058932	ICM	G03C001-492
	INCL	430270100
US 2005058932	NCL	430/270.100

OS MARPAT 142:325922
AB There is disclosed a compn. comprising a mixt. of endo- and exo-2-(bicyclo[2.2.1]hept-5-en-2-yl)-2,2-fluoroalkyl-ethan-2-ol

which is rich in the exo isomer, preferably the endo/exo concn. ratio is no greater than 5/95. The compn. is useful for forming a repeat unit of a polymer which polymer may further comprise addnl. repeat units derived from tert-Bu acrylate, hydroxyadamantyl acrylate, protected or unprotected fluorinated olefins, 2-methyl-2-adamantyl acrylate, 2-propenoic acid, 2-hydroxy-1,1,2-trimethylpropyl ester. Polymers of this invention are useful as the binder component of a photoresist compn. for microlithog.

ST photoresist microlithog synthesis

IT Lithography
(micron; prepn. of exo-2-fluoroalkyl(bicyclo[2.2.1]hept-5-enes) for photoresist)

IT Photoresists
(prepn. of exo-2-fluoroalkyl(bicyclo[2.2.1]hept-5-enes) for photoresist)

IT 848040-88-0P 848040-90-4P 848040-92-6P
(prepn. of exo-2-fluoroalkyl(bicyclo[2.2.1]hept-5-enes) for photoresist)

IT 848040-94-8P **848040-96-0P**
(prepn. of exo-2-fluoroalkyl(bicyclo[2.2.1]hept-5-enes) for photoresist)

IT 848040-78-8P 848040-80-2P 848040-84-6P 848040-86-8P
(prepn. of exo-2-fluoroalkyl(bicyclo[2.2.1]hept-5-enes) for photoresist compn.)

IT 196314-61-1P
(prepn. of exo-2-fluoroalkyl(bicyclo[2.2.1]hept-5-enes) for photoresist compn.)

IT 3721-19-5 4313-36-4, 5-Chloronorbornene 502136-03-0
(prepn. of exo-2-fluoroalkyl(bicyclo[2.2.1]hept-5-enes) for photoresist compn.)

IT **848040-96-0P**
(prepn. of exo-2-fluoroalkyl(bicyclo[2.2.1]hept-5-enes) for photoresist)

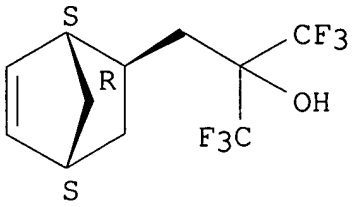
RN 848040-96-0 ZCAPLUS

CN 2-Propenoic acid, 3-hydroxytricyclo[3.3.1.13,7]dec-1-yl ester, polymer with rel-(1R,2S,4R)-.alpha.,.alpha.-bis(trifluoromethyl)bicyclo[2.2.1]hept-2-ene-2-ethanol, 2-hydroxy-1,1,2-trimethylpropyl 2-propenoate and tetrafluoroethene (9CI) (CA INDEX NAME)

CM 1

CRN 848040-92-6
CMF C11 H12 F6 O

Relative stereochemistry.



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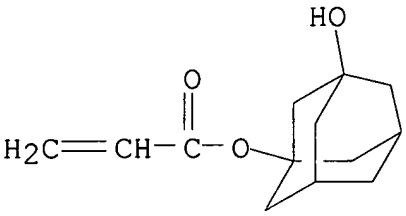
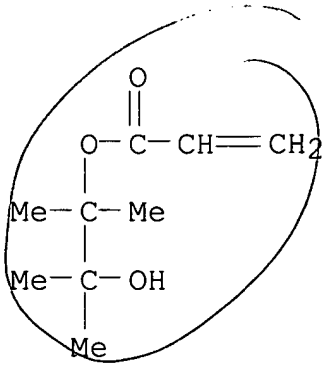
CRN 216581-76-9
CMF C13 H18 O3



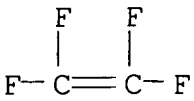
CM 3

CRN 97325-36-5
CMF C9 H16 O3



CM 4

CRN 116-14-3
CMF C2 F4



L6 ANSWER 4 OF 4 ZCAPLUS COPYRIGHT 2005 ACS on STN
AN 2004:326237 ZCAPLUS
DN 140:347511
ED Entered STN: 22 Apr 2004
TI Photoresists with hydroxylated, photoacid-cleavable groups
IN Farnham, William Brown; Feiring, Andrew L.; Schadt, Frank L., III; Qiu, Weiming
PA E.I. Du Pont de Nemours and Company, USA
SO Eur. Pat. Appl., 25 pp.
CODEN: EPXXDW
DT Patent
LA English
IC ICM G03F007-039
ICS G03F007-004
CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)
Section cross-reference(s): 35, 38

Applicant's

FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI EP 1411389	A1	20040421	EP 2003-256267	20031003
R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT, IE, SI, LT, LV, FI, RO, MK, CY, AL, TR, BG, CZ, EE, HU, SK				
US 2004126697	A1	20040701	US 2003-669492	20030924
JP 2004280049	A2	20041007	JP 2003-346258	20031003
PRAI US 2002-415855P	P	20021003		

CLASS

PATENT NO.	CLASS	PATENT FAMILY CLASSIFICATION CODES
EP 1411389	ICM	G03F007-039
	ICS	G03F007-004
US 2004126697	NCL	430/270.100
JP 2004280049	FTERM	2H025/AB16; 2H025/AC04; 2H025/AD01; 2H025/AD03; 2H025/BE00; 2H025/BG00; 2H025/CC03; 2H025/CC04;

2H025/CC20; 2H025/FA03; 2H025/FA12; 2H025/FA17;
4J100/AC23Q; 4J100/AC24Q; 4J100/AC25Q;
4J100/AC26Q; 4J100/AC27Q; 4J100/AC31Q;
4J100/AE09R; 4J100/AE39Q; 4J100/AG08R;
4J100/AJ02S; 4J100/AL03S; 4J100/AL08S;
4J100/AL09P; 4J100/AL09S; 4J100/AL10S;
4J100/AR09R; 4J100/AR11R; 4J100/BA02R;
4J100/BA02S; 4J100/BA03R; 4J100/BA10R;
4J100/BA20R; 4J100/BA40S; 4J100/BB07R;
4J100/BB12R; 4J100/BC08S; 4J100/BC09R;
4J100/BC09S; 4J100/CA06; 4J100/DA04; 4J100/DA25;
4J100/JA38

AB The present invention pertains to photoimaging and the use of photoresists (pos.-working and/or neg.-working) for imaging in the prodn. of semiconductor devices. The present invention also pertains to novel hydroxy ester-contg. polymer compns. that are useful as base resins in resists and potentially in many other applications.

ST photoresist hydroxylated photoacid semiconductor device

IT Photoresists
(photoresists with hydroxylated, photoacid-cleavable groups)

IT Semiconductor device fabrication
(photoresists with hydroxylated, photoacid-cleavable groups for)

IT 97325-36-5P
(prepn. of photoresists with hydroxylated, photoacid-cleavable groups)

IT **680975-27-3P 680975-29-5P 680975-30-8P**
(prepn. of photoresists with hydroxylated, photoacid-cleavable groups)

IT 76-09-5, Pinacol 814-68-6, Acryloyl chloride
(prepn. of photoresists with hydroxylated, photoacid-cleavable groups)

RE.CNT 2 THERE ARE 2 CITED REFERENCES AVAILABLE FOR THIS RECORD

RE

(1) Carbonell, R; US 2002119398 A1 2002 ZCAPLUS

(2) Koh, C; US 6387589 B1 2002 ZCAPLUS

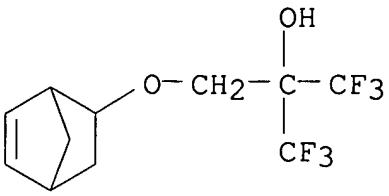
IT **680975-27-3P 680975-29-5P 680975-30-8P**
(prepn. of photoresists with hydroxylated, photoacid-cleavable groups)

RN 680975-27-3 ZCAPLUS

CN 2-Propenoic acid, 2-hydroxy-1,1,2-trimethylpropyl ester, polymer with 2-[(bicyclo[2.2.1]hept-5-en-2-yloxy)methyl]-1,1,1,3,3,3-hexafluoro-2-propanol and tetrafluoroethene (9CI) (CA INDEX NAME)

CM 1

CRN 305815-63-8
CMF C11 H12 F6 O2



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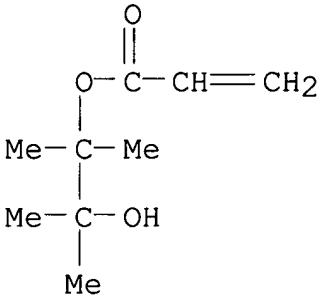
CRN 97325-36-5
CMF C9 H16 O3



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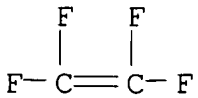
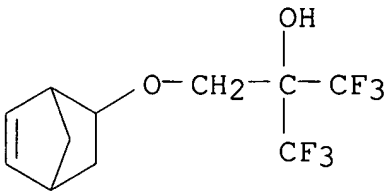
CRN 116-14-3
CMF C2 F4



RN 680975-29-5 ZCAPLUS
CN 2-Propenoic acid, 1,1-dimethylethyl ester, polymer with 2-[(bicyclo[2.2.1]hept-5-en-2-yloxy)methyl]-1,1,1,3,3,3-hexafluoro-2-propanol, 2-hydroxy-1,1,2-trimethylpropyl 2-propenoate and tetrafluoroethene (9CI) (CA INDEX NAME)

CM 1

CRN 305815-63-8
CMF C11 H12 F6 O2



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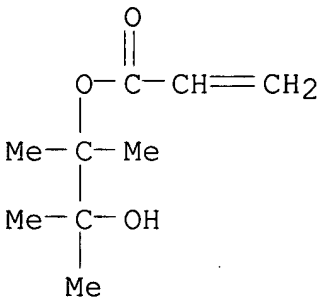
CRN 97325-36-5
CMF C9 H16 O3



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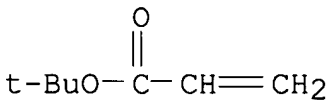
CRN 1663-39-4
CMF C7 H12 O2



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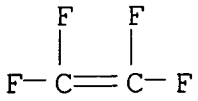
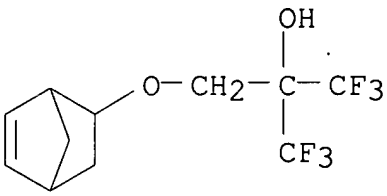
CRN 116-14-3
CMF C2 F4



RN 680975-30-8 ZCAPLUS
CN 2-Propenoic acid, 2-hydroxy-1,1,2-trimethylpropyl ester, polymer with 2-[(bicyclo[2.2.1]hept-5-en-2-yloxy)methyl]-1,1,1,3,3,3-hexafluoro-2-propanol, 2-methyltricyclo[3.3.1.13,7]dec-2-yl 2-propenoate and tetrafluoroethene (9CI) (CA INDEX NAME)

CM 1

CRN 305815-63-8
CMF C11 H12 F6 O2



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CRN 249562-06-9
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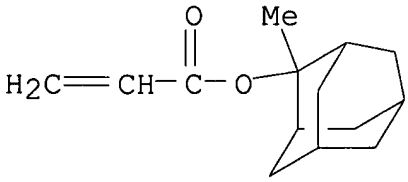
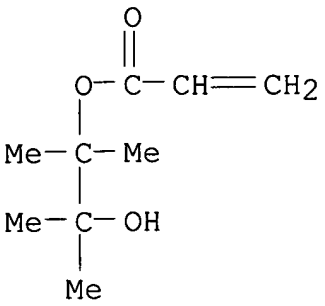


CM 3

CRN 97325-36-5
CMF C9 H16 O3



CM 4

CRN 116-14-3
CMF C2 F4